STARPOWER

SEMICONDUCTOR **IGBT**

GD600HFT120C2S_G8

1200V/600A 2 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverter and UPS.

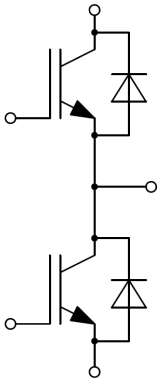
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- 10μs short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings T_C=25°C unless otherwise noted

IGBT

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	±30	V
I_C	Collector Current @ T_C=25°C @ T_C=100°C	970 600	A
I_{CM}	Pulsed Collector Current t_p=1ms	1200	A
P_D	Maximum Power Dissipation @ T_j=175°C	3260	W

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	600	A
I_{FM}	Diode Maximum Forward Current t_p=1ms	1200	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	175	°C
T_{jop}	Operating Junction Temperature	-40 to +150	°C
T_{STG}	Storage Temperature Range	-40 to +125	°C
V_{ISO}	Isolation Voltage RMS,f=50Hz,t=1min	4000	V

IGBT Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C=600A,V_{GE}=15V, T_j=25°C		1.70	2.15	V
		I_C=600A,V_{GE}=15V, T_j=125°C		1.95		
		I_C=600A,V_{GE}=15V, T_j=150°C		2.00		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	I_C=24.0mA,V_{CE}=V_{GE}, T_j=25°C	5.0	5.6	6.5	V
I_{CES}	Collector Cut-Off Current	V_{CE}=V_{CES},V_{GE}=0V, T_j=25°C			5.0	mA
I_{GES}	Gate-Emitter Leakage Current	V_{GE}=V_{GES},V_{CE}=0V, T_j=25°C			400	nA
R_{Gint}	Internal Gate Resistance			0.67		Ω
C_{ies}	Input Capacitance	V_{CE}=30V,f=1MHz, V_{GE}=0V		51.0		nF
C_{res}	Reverse Transfer Capacitance			1.65		nF
Q_G	Gate Charge	V_{GE}=15V		3.21		μC
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=600A, R_G=1.1Ω,V_{GE}=±15V, T_j=25°C		332		ns
t_r	Rise Time			106		ns
$t_{d(off)}$	Turn-Off Delay Time			525		ns
t_f	Fall Time			125		ns
E_{on}	Turn-On Switching Loss			12.6		mJ
E_{off}	Turn-Off Switching Loss			54.6		mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=600A, R_G=1.1Ω,V_{GE}=±15V, T_j=125°C		335		ns
t_r	Rise Time			110		ns
$t_{d(off)}$	Turn-Off Delay Time			575		ns
t_f	Fall Time			168		ns
E_{on}	Turn-On Switching Loss			21.2		mJ
E_{off}	Turn-Off Switching Loss			69.2		mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=600A, R_G=1.1Ω,V_{GE}=±15V, T_j=150°C		340		ns
t_r	Rise Time			112		ns
$t_{d(off)}$	Turn-Off Delay Time			586		ns
t_f	Fall Time			185		ns
E_{on}	Turn-On Switching Loss			22.9		mJ
E_{off}	Turn-Off Switching Loss			74.0		mJ
I_{SC}	SC Data	t_P≤10μs,V_{GE}=15V, T_j=150°C,V_{CC}=900V, V_{CEM}≤1200V		2400		A

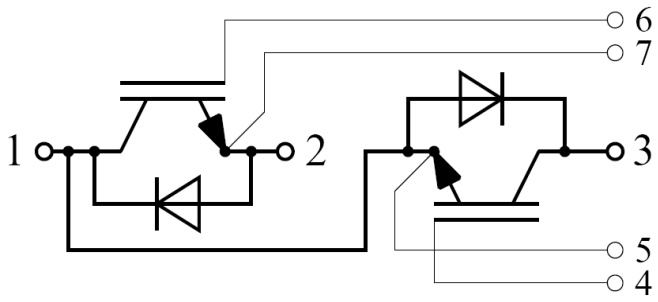
Diode Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	I_F=600A,V_{GE}=0V,T_j=25°C		1.65	2.10	V
		I_F=600A,V_{GE}=0V,T_j=125°C		1.65		
		I_F=600A,V_{GE}=0V,T_j=150°C		1.65		
Q_r	Recovered Charge	V_{CC}=600V,I_F=600A, -di/dt=5000A/μs,V_{GE}=-15V, T_j=25°C		62.6		μC
I_{RM}	Peak Reverse Recovery Current			292		A
E_{rec}	Reverse Recovery Energy			22.6		mJ
Q_r	Recovered Charge	V_{CC}=600V,I_F=600A, -di/dt=5000A/μs,V_{GE}=-15V, T_j=125°C		116		μC
I_{RM}	Peak Reverse Recovery Current			424		A
E_{rec}	Reverse Recovery Energy			44.8		mJ
Q_r	Recovered Charge	V_{CC}=600V,I_F=600A, -di/dt=5000A/μs,V_{GE}=-15V, T_j=150°C		132		μC
I_{RM}	Peak Reverse Recovery Current			454		A
E_{rec}	Reverse Recovery Energy			51.7		mJ

Module Characteristics T_C=25°C unless otherwise noted

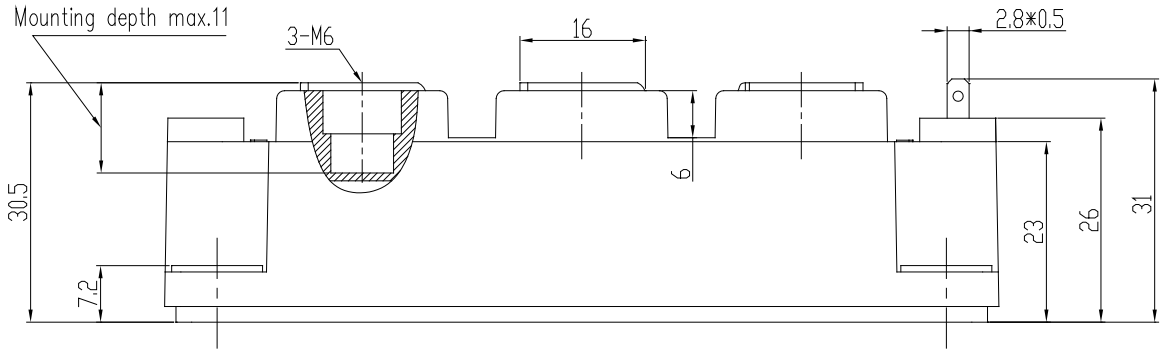
Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance			20	nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		0.35		mΩ
R_{thJC}	Junction-to-Case (per IGBT) Junction-to-Case (per Diode)			0.046 0.078	K/W
R_{thCH}	Case-to-Heatsink (per IGBT) Case-to-Heatsink (per Diode) Case-to-Heatsink (per Module)		0.111 0.189 0.035		K/W
M	Terminal Connection Torque, Screw M6 Mounting Torque, Screw M6	2.5 3.0		5.0 5.0	N.m
G	Weight of Module		300		g

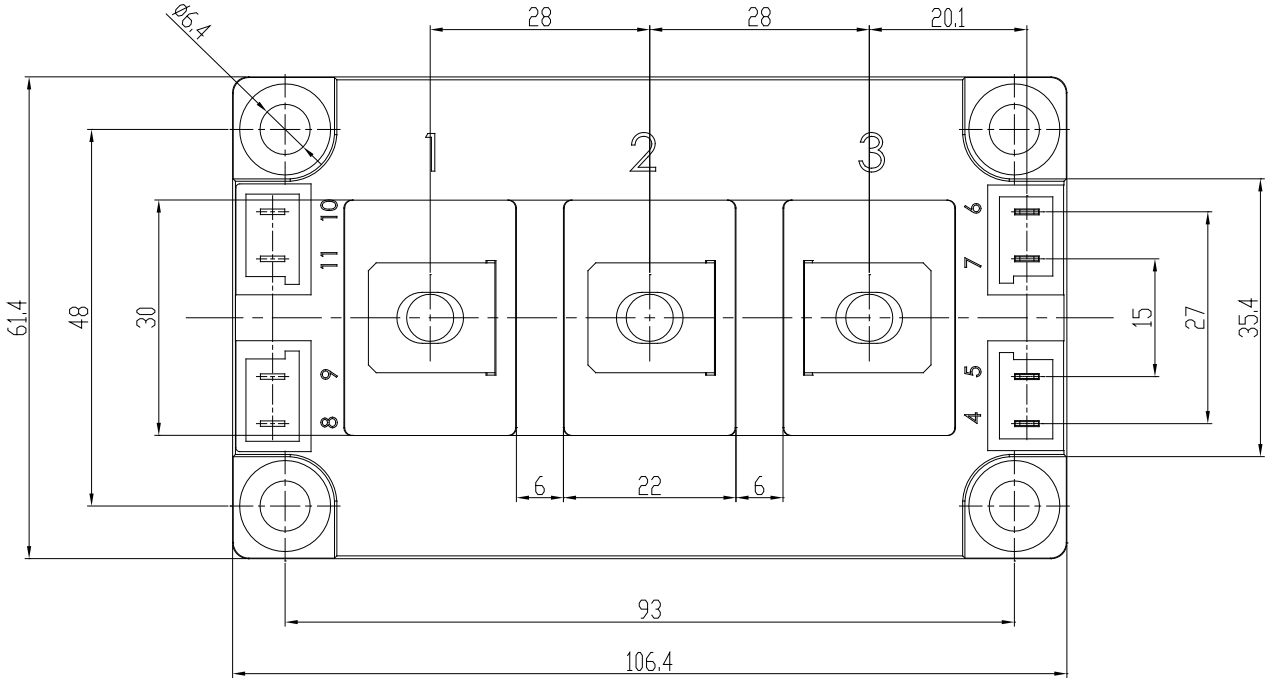
Circuit Schematic



Package Dimensions

Dimensions in Millimeters





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